

(Use several sheets if necessary)

Application Number

10/756,568 ✓

Seiki Ogura et al.

01/13/04

Group Art Unit

2827 ✓

[illegible][illegible]

TL	-	Chang et al., "A New Sense Memory Using Source-Side Injection for Programming," IEEE Electron Device Letters, Vol. 19, No. 7, pp. 253-255, July 1998.
TL	-	Ogura et al., "Low Voltage, Low Current, High Speed Program Step Split Gate Cell with Ballistic Direct Injection for EEPROM/Flash," TIEDM 1998, p. 987
EXAMINER	Doyle ✓ <div style="float: right;">DATE CONSIDERED 5/18/05 ✓</div>	

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.